

RJK6026DPP

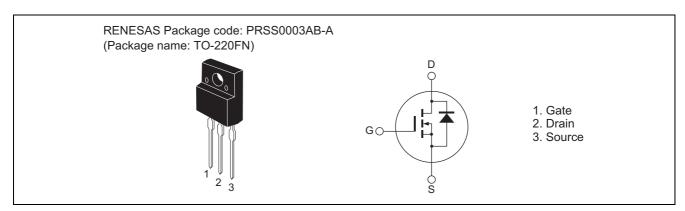
Silicon N Channel MOS FET High Speed Power Switching

REJ03G1592-0200 Rev.2.00 Jun 04, 2008

Features

- Low on-resistance
- Low leakage current
- High speed switching

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

| Item | Symbol | Ratings | Unit |
|---|-------------------------------|-------------|------|
| Drain to source voltage | V_{DSS} | 600 | V |
| Gate to source voltage | V_{GSS} | ±30 | V |
| Drain current | I _D Note4 | 5 | А |
| Drain peak current | I _{D (pulse)} Note1 | 20 | А |
| Body-drain diode reverse drain current | I _{DR} | 5 | А |
| Body-drain diode reverse drain peak current | I _{DR (pulse)} Note1 | 20 | А |
| Avalanche current | I _{AP} Note3 | 4 | А |
| Avalanche energy | E _{AR} Note3 | 0.87 | mJ |
| Channel dissipation | Pch Note2 | 28.5 | W |
| Channel to case thermal impedance | θch-c | 4.38 | °C/W |
| Channel temperature | Tch | 150 | °C |
| Storage temperature | Tstg | -55 to +150 | °C |

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

- 2. Value at Tc = 25°C
- 3. STch = 25° C, Tch $\leq 150^{\circ}$ C
- 4. Limited by maximum safe operation area

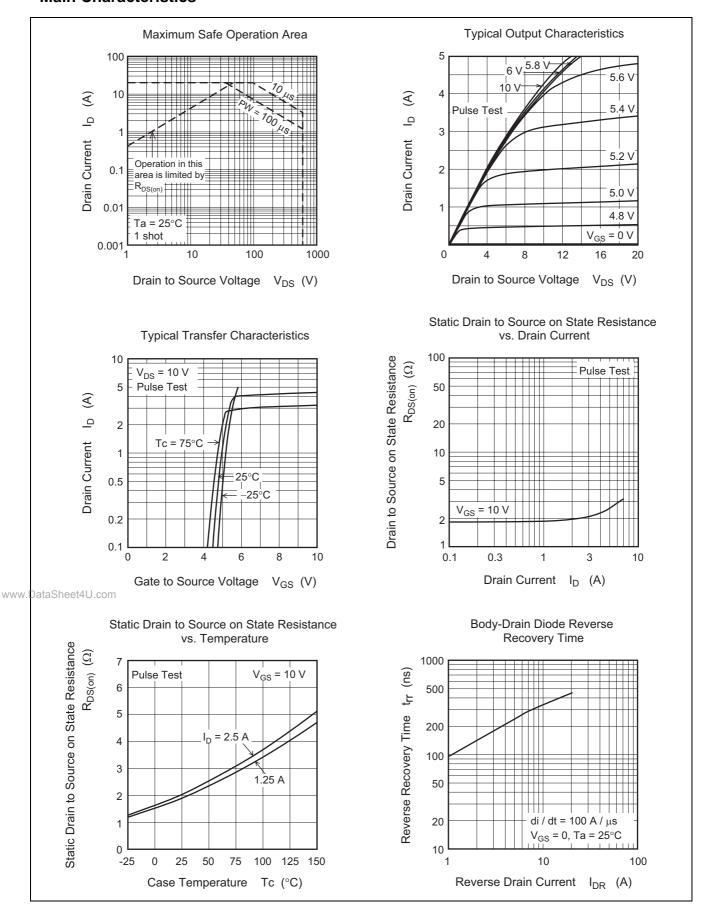
Electrical Characteristics

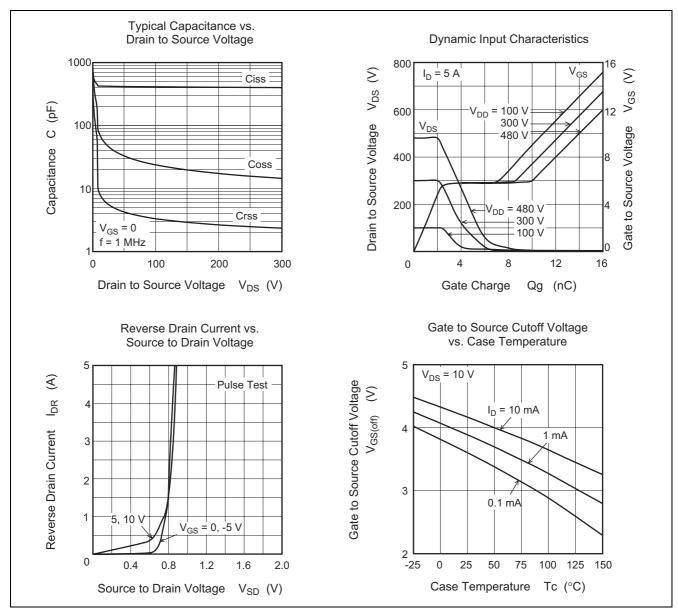
 $(Ta = 25^{\circ}C)$

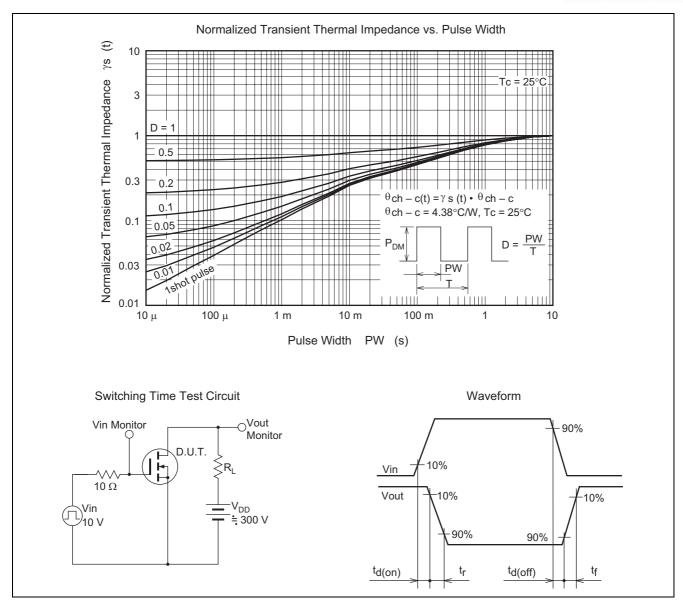
| Item | Symbol | Min | Тур | Max | Unit | Test conditions |
|--|---------------------|-----|-----|------|------|--|
| Drain to source breakdown voltage | $V_{(BR)DSS}$ | 600 | _ | _ | V | $I_D = 10 \text{ mA}, V_{GS} = 0$ |
| Zero gate voltage drain current | I _{DSS} | | _ | 1 | μΑ | $V_{DS} = 600 \text{ V}, V_{GS} = 0$ |
| Gate to source leak current | I _{GSS} | | _ | ±0.1 | μΑ | $V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$ |
| Gate to source cutoff voltage | $V_{GS(off)}$ | 3.0 | _ | 4.5 | V | $V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$ |
| Static drain to source on state resistance | R _{DS(on)} | _ | 2.0 | 2.4 | Ω | $I_D = 2.5 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note5}}$ |
| Input capacitance | Ciss | _ | 440 | _ | pF | V _{DS} = 25 V |
| Output capacitance | Coss | _ | 45 | _ | pF | $V_{GS} = 0$ |
| Reverse transfer capacitance | Crss | _ | 6 | _ | pF | f = 1 MHz |
| Turn-on delay time | t _{d(on)} | _ | 26 | _ | ns | I _D = 2.5 A |
| Rise time | t _r | _ | 18 | _ | ns | V _{GS} = 10 V |
| Turn-off delay time | $t_{d(off)}$ | _ | 53 | _ | ns | $R_L = 120 \Omega$ |
| Fall time | t _f | _ | 14 | _ | ns | $Rg = 10 \Omega$ |
| Total gate charge | Qg | _ | 14 | _ | nC | V _{DD} = 480 V |
| Gate to source charge | Qgs | _ | 3 | _ | nC | V _{GS} = 10 V I _D = 5 A |
| Gate to drain charge | Qgd | _ | 7 | _ | nC | |
| Body-drain diode forward voltage | V_{DF} | _ | 0.9 | 1.5 | V | $I_F = 5 \text{ A}, V_{GS} = 0^{\text{Note5}}$ |
| Body-drain diode reverse recovery time | t _{rr} | | 250 | _ | ns | $I_F = 5 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$ |

Notes: 5. Pulse test

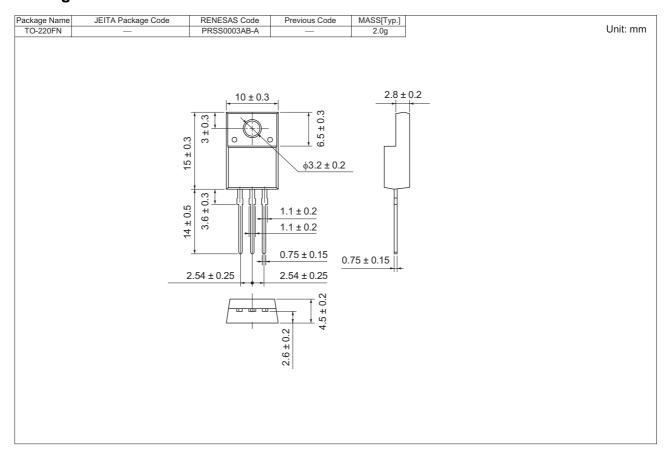
Main Characteristics







Package Dimensions



Ordering Information

| Part No. | Quantity | Shipping Container |
|------------------|----------|--------------------|
| RJK6026DPP-00-T2 | 1050 pcs | Box (Tube) |

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